



PNP Silicon Low-Power Transistor

Qualified per MIL-PRF-19500/485

Qualified Levels:
JAN, JANTX, JANTXV
and JANS

DESCRIPTION

This family of 2N5415UA and 2N5416UA epitaxial planar transistors are military qualified up to a JANS level for high-reliability applications. The UA package is hermetically sealed and provides a low profile for minimizing board height. These devices are also available in the long-leaded TO-5, short-leaded TO-39 and low profile U4 packaging.

Important: For the latest information, visit our website <http://www.microsemi.com>.

FEATURES

- JEDEC registered 2N5415 through 2N5416 series
- JAN, JANTX, JANTXV, and JANS qualifications are available per MIL-PRF-19500/485. (See [part nomenclature](#) for all available options.)
- RoHS compliant

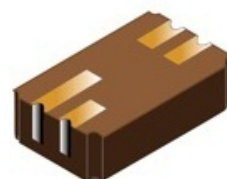
APPLICATIONS / BENEFITS

- General purpose transistors for low power applications requiring high frequency switching.
- Low package profile
- Military and other high-reliability applications

MAXIMUM RATINGS @ $T_A = +25^\circ\text{C}$ unless otherwise noted

Parameters / Test Conditions	Symbol	2N5415UA	2N5416UA	Unit
Collector-Emitter Voltage	V_{CEO}	200	300	V
Collector-Base Voltage	V_{CBO}	200	350	V
Emitter-Base Voltage	V_{EBO}	6.0	6.0	V
Collector Current	I_C	1.0	1.0	A
Operating & Storage Junction Temperature Range	T_J, T_{stg}	-65 to +200		$^\circ\text{C}$
Thermal Resistance Junction-to-Ambient	$R_{\theta JA}$	234		$^\circ\text{C/W}$
Thermal Resistance Junction-to-Solder Pad	$R_{\theta JSP}$	80		$^\circ\text{C/W}$
Total Power Dissipation @ $T_A = +25^\circ\text{C}$ ⁽¹⁾ @ $T_{SP} = +25^\circ\text{C}$ ⁽²⁾	P_T	0.75 2		W


Notes: 1. Derate linearly 4.29 mW/ $^\circ\text{C}$ for $T_A > +25^\circ\text{C}$
2. Derate linearly 12.5 mW/ $^\circ\text{C}$ for $T_{SP} > +25^\circ\text{C}$




UA Package

Also available in:


TO-5 package
(long-leaded)

 [2N5415 – 2N5416](#)

TO-39 (TO-205AD)
package
(short-leaded)

 [2N5415S – 2N5416S](#)

U4 package
(surface mount)

 [2N5415U4 – 2N5416U4](#)

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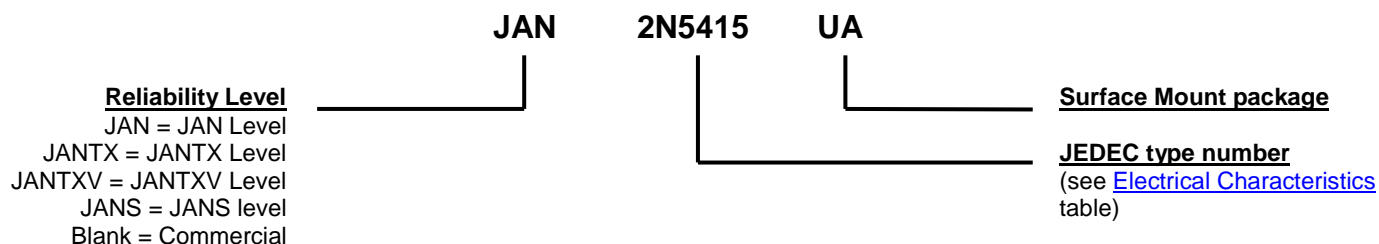
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MECHANICAL and PACKAGING

- CASE: Hermetically sealed ceramic package
- TERMINALS: Gold plate over nickel
- MARKING: Manufacturer's ID, date code, part number
- POLARITY: PNP (see package outline)
- TAPE & REEL option: Per EIA-481 (consult factory for quantities)
- WEIGHT: Approximately 0.12 grams
- See [Package Dimensions](#) on last page.

PART NOMENCLATURE

SYMBOLS & DEFINITIONS

Symbol	Definition
C_{obo}	Common-base open-circuit output capacitance
I_{CEO}	Collector cutoff current, base open
I_{CEX}	Collector cutoff current, circuit between base and emitter
I_{EBO}	Emitter cutoff current, collector open
h_{FE}	Common-emitter static forward current transfer ratio
V_{CEO}	Collector-emitter voltage, base open
V_{CBO}	Collector-emitter voltage, emitter open
V_{EBO}	Emitter-base voltage, collector open

ELECTRICAL CHARACTERISTICS @ $T_A = +25\text{ }^{\circ}\text{C}$, unless otherwise noted
OFF CHARACTERISTICS

Parameters / Test Conditions	Symbol	Min.	Max.	Unit
Collector-Emitter Breakdown Voltage $I_C = 50\text{ mA}$, $I_B = 5\text{ mA}$, $L = 25\text{ mH}$; $f = 30 - 60\text{ Hz}$	$V_{(BR)CEO}$	200 300		V
Emitter-Base Cutoff Current $V_{EB} = 6.0\text{ V}$	I_{EBO}		20	μA
Collector-Emitter Cutoff Current $V_{CE} = 200\text{ V}$, $V_{BE} = 1.5\text{ V}$ $V_{CE} = 300\text{ V}$, $V_{BE} = 1.5\text{ V}$	I_{CEX}		50	μA
Collector-Emitter Cutoff Current $V_{CE} = 150\text{ V}$ $V_{CE} = 250\text{ V}$	I_{CEO1}		50	μA
Collector-Emitter Cutoff Current $V_{CE} = 200\text{ V}$ $V_{CE} = 300\text{ V}$	I_{CEO2}		1	mA
Collector-Base Cutoff Current $V_{CB} = 175\text{ V}$ $V_{CB} = 280\text{ V}$	I_{CBO1}		50	μA
$V_{CB} = 200\text{ V}$ $V_{CB} = 350\text{ V}$	I_{CBO2}		500	μA
$V_{CB} = 175\text{ V}$, $T_A = +150\text{ }^{\circ}\text{C}$ $V_{CB} = 280\text{ V}$, $T_A = +150\text{ }^{\circ}\text{C}$	I_{CBO3}		1	mA

ON CHARACTERISTICS

Parameters / Test Conditions	Symbol	Min.	Max.	Unit
Forward-Current Transfer Ratio $I_C = 50\text{ mA}$, $V_{CE} = 10\text{ V}$ $I_C = 1\text{ mA}$, $V_{CE} = 10\text{ V}$ $I_C = 50\text{ mA}$, $V_{CE} = 10\text{ V}$, $T_A = +150\text{ }^{\circ}\text{C}$	h_{FE}	30 15 15	120	
Collector-Emitter Saturation Voltage $I_C = 50\text{ mA}$, $I_B = 5\text{ mA}$	$V_{CE(sat)}$		2.0	V
Base-Emitter Voltage Non-Saturation $I_C = 50\text{ mA}$, $V_{CE} = 10\text{ V}$	V_{BE}		1.5	V

DYNAMIC CHARACTERISTICS

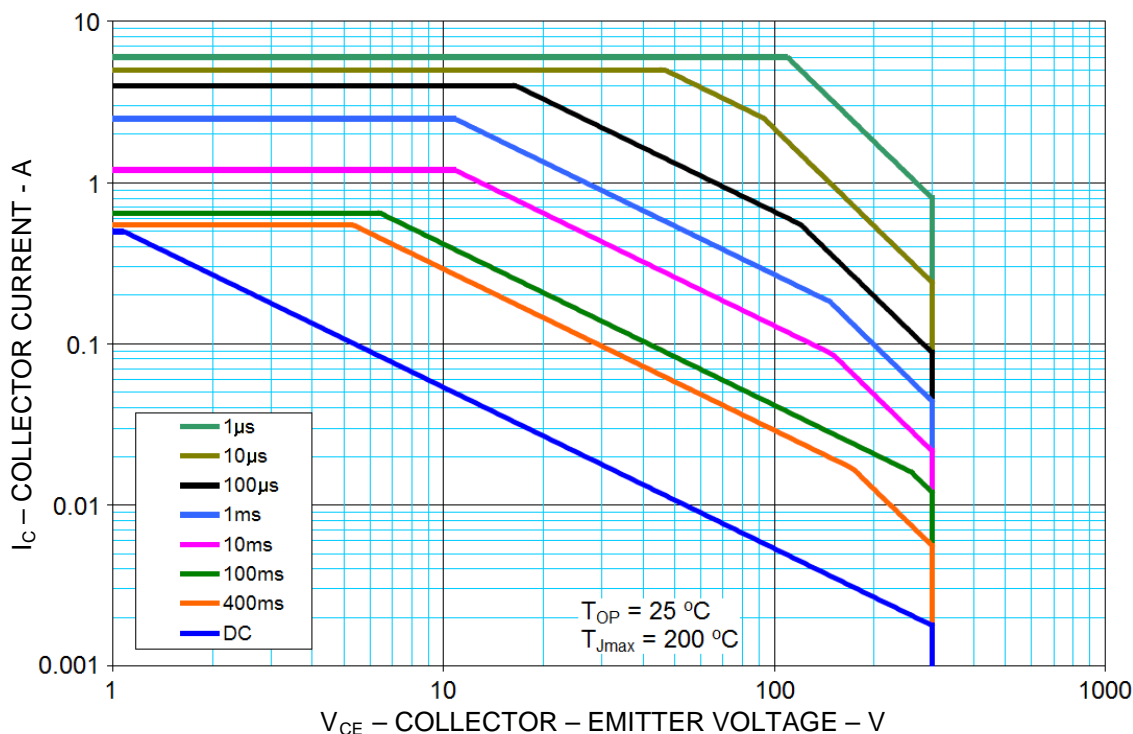
Parameters / Test Conditions	Symbol	Min.	Max.	Unit
Magnitude of Common Emitter Small-Signal Short-Circuit Forward Current Transfer Ratio $I_C = 10\text{ mA}$, $V_{CE} = 10\text{ V}$, $f = 5\text{ MHz}$	$ h_{fe} $	3	15	
Small-signal short Circuit Forward-Current Transfer Ratio $I_C = 5\text{ mA}$, $V_{CE} = 10\text{ V}$, $f \leq 1\text{ kHz}$	h_{fe}	25		
Output Capacitance $V_{CB} = 10\text{ V}$, $I_E = 0$, $100\text{ kHz} \leq f \leq 1\text{ MHz}$	C_{obo}		15	pF

ELECTRICAL CHARACTERISTICS @ $T_A = +25\text{ }^{\circ}\text{C}$ unless otherwise noted. (continued)
SWITCHING CHARACTERISTICS

Parameters / Test Conditions	Symbol	Min.	Max.	Unit
Turn-On Time $V_{CC} = 200\text{ V}$, $I_C = 50\text{ mA}$, $I_{B1} = 5\text{ mA}$	t_{on}		1	μs
Turn-Off Time $V_{CC} = 200\text{ V}$, $I_C = 50\text{ mA}$, $I_{B1} = I_{B2} = 5\text{ mA}$	t_{off}		10	μs

SAFE OPERATING AREA (See SOA graph below and [MIL-STD-750, method 3053](#))

DC Tests
 $T_C = +25\text{ }^{\circ}\text{C}$, $t_P = 0.4\text{ s}$, 1 Cycle

Test 1
 $V_{CE} = 10\text{ V}$, $I_C = 0.3\text{ A}$
Test 2
 $V_{CE} = 100\text{ V}$, $I_C = 30\text{ mA}$
Test 3 (2N5415UA only)
 $V_{CE} = 200\text{ V}$, $I_C = 12\text{ mA}$
Test 4 (2N5416UA only)
 $V_{CE} = 300\text{ V}$, $I_C = 5\text{ mA}$

Maximum Safe Operating Area ($T_J = 200\text{ }^{\circ}\text{C}$)

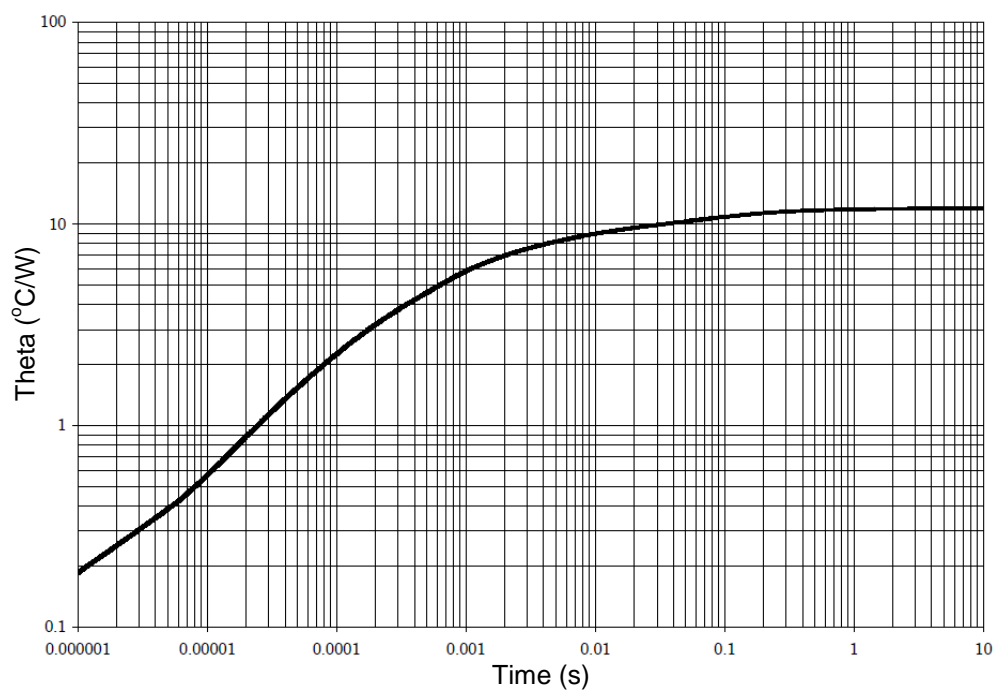
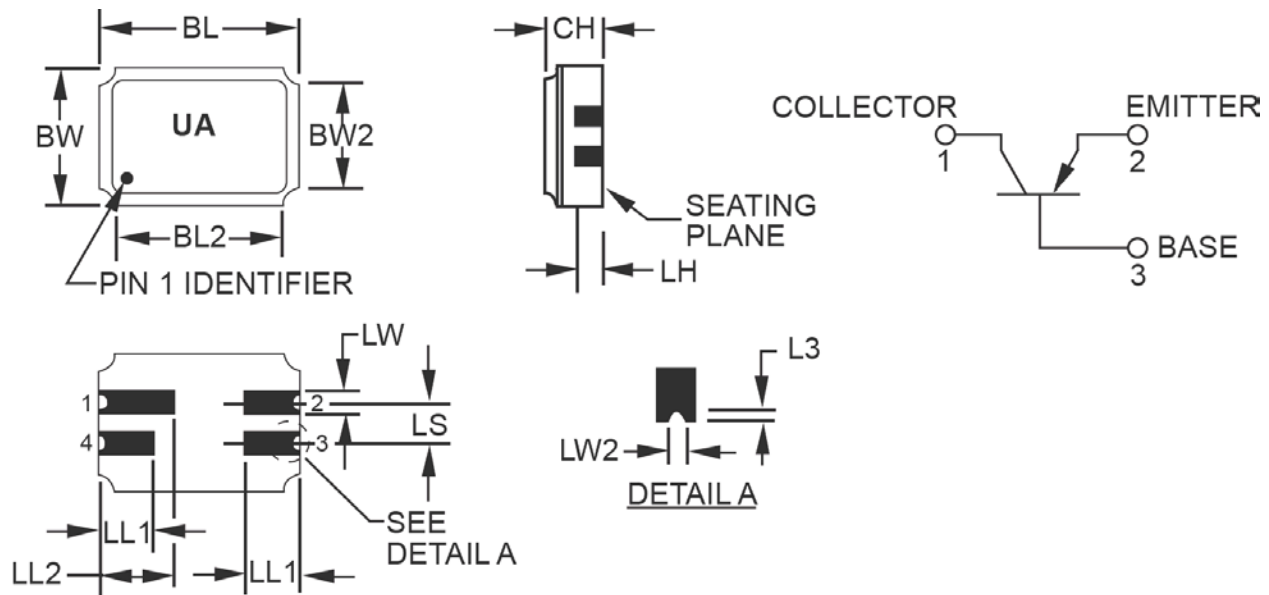
GRAPHS


FIGURE 1
Thermal impedance graph ($R_{\theta JA}$)

PACKAGE DIMENSIONS

NOTES:

1. Dimensions are in inches.
2. Millimeters are given for information only.
3. Dimension "CH" controls the overall package thickness. When a window lid is used, dimension "CH" must increase by a minimum of 0.010 inch (0.254 mm) and a maximum of 0.040 inch (1.020 mm).
4. The corner shape (square, notch, radius, etc.) may vary at the manufacturer's option, from that shown on the drawing.
5. Dimensions "LW2" minimum and "L3" minimum and the appropriate castellation length define an unobstructed three-dimensional space traversing all of the ceramic layers in which a castellation was designed. (Castellations are required on bottom two layers, optional on top ceramic layer.) Dimension "LW2" maximum and "L3" maximum define the maximum width and depth of the castellation at any point on its surface. Measurement of these dimensions may be made prior to solder dipping.
6. The co-planarity deviation of all terminal contact points, as defined by the device seating plane, shall not exceed 0.006 inch (0.15mm) for solder dipped leadless chip carriers.
7. In accordance with ASME Y14.5M, diameters are equivalent to Φ x symbology.

Symbol	Dimensions				Note
	Inches		Millimeters		
	Min	Max	Min	Max	
BL	0.215	0.225	5.46	5.71	
BL2	-	0.225	-	5.71	
BW	0.145	0.155	3.68	3.93	
BW2	-	0.155	-	3.93	
CH	0.061	0.075	1.55	1.90	3
L3	0.003	0.007	0.08	0.18	5
LH	0.029	0.042	0.74	1.07	
LL1	0.032	0.048	0.81	1.22	
LL2	0.072	0.088	1.83	2.23	
LS	0.045	0.055	1.14	1.39	
LW	0.022	0.028	0.56	0.71	
LW2	0.006	0.022	0.15	0.56	5
Pin no.		1	2	3	4
Transistor		Collector	Emitter	Base	N/C